74HC175; 74HCT175

Quad D-type flip-flop with reset; positive-edge trigger

Rev. 4 — 8 April 2014 Product data sheet

1. General description

The 74HC175; 74HCT175 are quad positive edge-triggered D-type flip-flops with individual data inputs (Dn) and both Qn and $\overline{Q}$n outputs. The common clock (CP) and master reset ($\overline{MR}$) inputs load and reset all flip-flops simultaneously. The D-input that meets the set-up and hold time requirements on the LOW-to-HIGH clock transition is stored in the flip-flop and appears at the Q output. A LOW on $\overline{MR}$ causes the flip-flops and outputs to be reset LOW.

The device is useful for applications where both the true and complement outputs are required and the clock and master reset are common to all storage elements.

2. Features and benefits

- Input levels:
  - For 74HC175: CMOS level
  - For 74HCT175: TTL level
- Four edge-triggered D-type flip-flops
- Asynchronous master reset
- Complies with JEDEC standard no. 7A
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V.
- Multiple package options
- Specified from −40 °C to +85 °C and −40 °C to +125 °C.

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC175N	−40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
74HCT175N				
74HC175D	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT175D				
74HC175DB	−40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT175DB				
74HC175PW	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT175PW				

4. Functional diagram

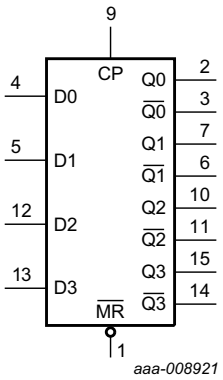


Fig 1. Logic symbol

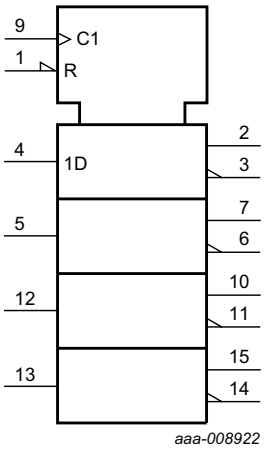


Fig 2. IEC logic symbol

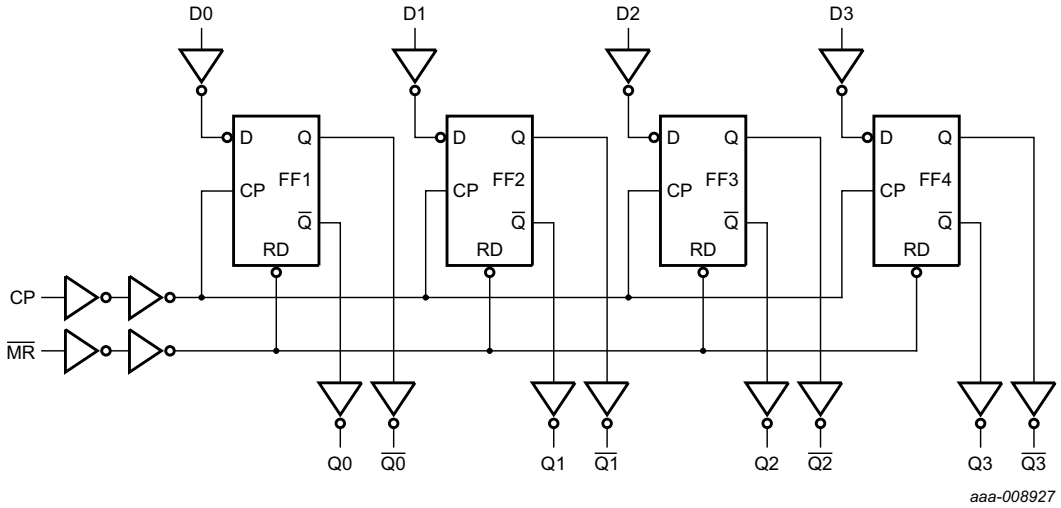


Fig 3. Logic diagram

5. Pinning information

5.1 Pinning

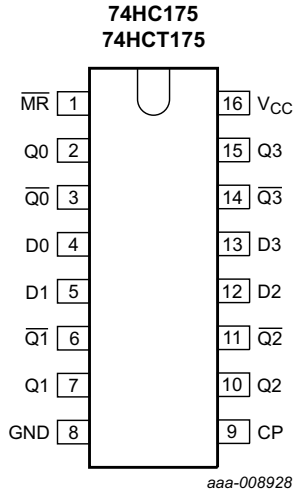


Fig 4. Pin configuration DIP16

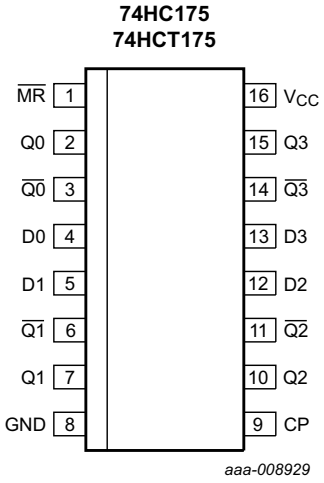


Fig 5. Pin configuration SO16

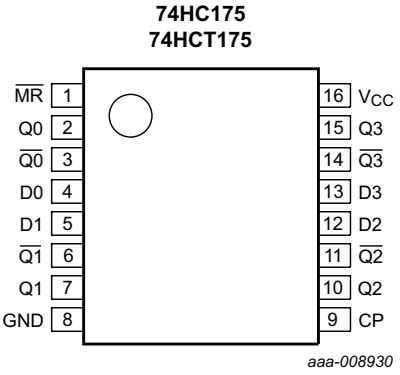


Fig 6. Pin configuration SSOP16 and TSSOP16

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$\overline{MR}$	1	asynchronous master reset input (active LOW)
Q0 to Q3	2, 7, 10, 15	flip-flop output
$\overline{Q0}$ to $\overline{Q3}$	3, 6, 11, 14	complementary flip-flop output
D0 to D3	4, 5, 12, 13	data input
GND	8	ground (0 V)
CP	9	clock input (LOW-to-HIGH edge-triggered)
V_{CC}	16	positive supply voltage

6. Functional description

Table 3. Function table[1]

Operating modes	Inputs			Outputs	
	$\overline{MR}$	CP	Dn	Qn	$\overline{Qn}$
reset (clear)	L	X	X	L	H
load “1”	H	↑	h	H	L
load “0”	H	↑	l	L	H

[1] H = HIGH voltage level;
h = HIGH voltage level one set-up time prior to the LOW-to-HIGH clock transition;
L = LOW voltage level;
l = LOW voltage level one set-up time prior to the LOW-to-HIGH clock transition;
X = don’t care;
↑ = LOW-to-HIGH clock transition.

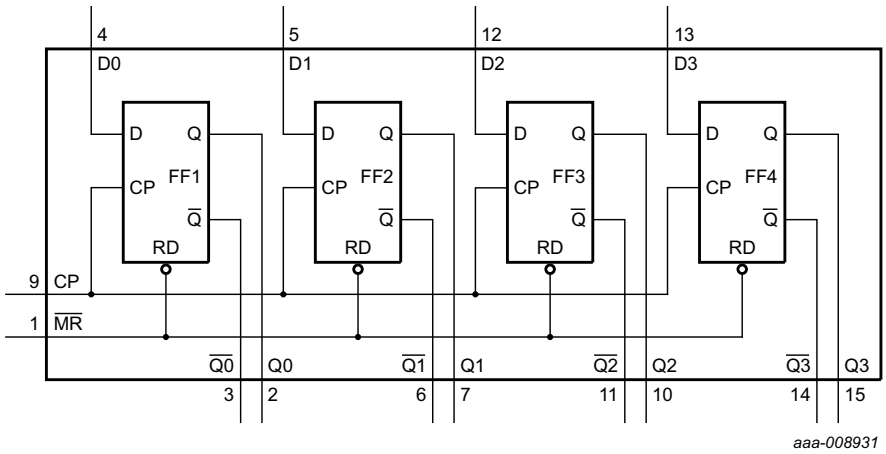


Fig 7. Functional diagram

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		−0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V	-	±20	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	-	±20	mA
I_O	output current	-0.5 V $< V_O < V_{CC} + 0.5$ V	-	±25	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		−50	-	mA
T_{stg}	storage temperature		−65	+150	°C

Table 4. Limiting values *...continued*

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	Min	Max	Unit
P_{tot}	total power dissipation	T_{amb} = −40 °C to +125 °C			
		DIP16 package [1]	-	750	mW
		SO16, SSOP16 and TSSOP16 [2]	-	500	mW

[1] For DIP16 package: above 70 °C the value of P_{tot} derates linearly with 12 mW/K.

[2] For SO16 package: above 70 °C the value of P_{tot} derates linearly with 8 mW/K.
For SSOP16 and TSSOP16 packages: above 60 °C the value of P_{tot} derates linearly with 5.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC175			74HCT175			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		−40	-	+125	−40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V_{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V_{CC} = 6.0 V	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC175										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V_{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V_{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V_{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V_{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = −20 μA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = −20 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = −20 μA; V_{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I_O = −4.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_O = −5.2 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V

Table 6. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}								
		I_O = 20 μA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_O = 5.2 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 6.0 V	-	-	±0.1	-	±1	-	±1	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	8.0	-	80	-	160	μA
C_I	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT175										
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = –20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –4.0 mA	3.98	4.32	-	3.84	-	3.7	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = 20 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 5.2 mA; V_{CC} = 5.5 V	-	0.15	0.26	-	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 5.5 V	-	-	±0.1	-	±1	-	±1	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	8.0	-	80	-	160	μA
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1$ V; other inputs at V_{CC} or GND; V_{CC} = 4.5 V to 5.5 V								
		Dn input	-	40	144	-	180	-	196	μA
		CP input	-	60	216	-	270	-	294	μA
		$\overline{MR}$ input	-	100	360	-	450	-	490	μA
C_I	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit, see Figure 11

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC175										
t_{pd}	propagation delay	CP to Qn, $\overline{Q}$n; see Figure 8 [1]								
		V_{CC} = 2.0 V	-	55	175	-	220	-	265	ns
		V_{CC} = 4.5 V	-	20	35	-	44	-	53	ns
		V_{CC} = 5 V; C_L = 15 pF	-	17	-	-	-	-	-	ns
		V_{CC} = 6.0 V	-	16	30	-	37	-	45	ns
t_{PHL}	HIGH to LOW propagation delay	$\overline{MR}$ to Qn, $\overline{Q}$n; see Figure 10								
		V_{CC} = 2.0 V	-	50	150	-	190	-	225	ns
		V_{CC} = 4.5 V	-	18	30	-	38	-	45	ns
		V_{CC} = 5 V; C_L = 15 pF	-	15	-	-	-	-	-	ns
		V_{CC} = 6.0 V	-	14	26	-	33	-	38	ns
t_t	transition time	Qn output; see Figure 8 [2]								
		V_{CC} = 2.0 V	-	19	75	-	95	-	110	ns
		V_{CC} = 4.5 V	-	7	15	-	19	-	22	ns
		V_{CC} = 6.0 V	-	6	13	-	16	-	19	ns
t_W	pulse width	CP input HIGH or LOW; see Figure 8								
		V_{CC} = 2.0 V	80	22	-	100	-	120	-	ns
		V_{CC} = 4.5 V	16	8	-	20	-	24	-	ns
		V_{CC} = 6.0 V	14	6	-	17	-	20	-	ns
		$\overline{MR}$ input LOW; see Figure 10								
		V_{CC} = 2.0 V	80	19	-	100	-	120	-	ns
		V_{CC} = 4.5 V	16	7	-	20	-	24	-	ns
		V_{CC} = 6.0 V	14	6	-	17	-	20	-	ns
t_{rec}	recovery time	$\overline{MR}$ to CP; see Figure 10								
		V_{CC} = 2.0 V	5	–33	-	5	-	5	-	ns
		V_{CC} = 4.5 V	5	–12	-	5	-	5	-	ns
		V_{CC} = 6.0 V	5	–10	-	5	-	5	-	ns
t_{su}	set-up time	Dn to CP; see Figure 8								
		V_{CC} = 2.0 V	80	3	-	100	-	120	-	ns
		V_{CC} = 4.5 V	16	1	-	20	-	24	-	ns
		V_{CC} = 6.0 V	14	1	-	17	-	20	-	ns

Table 7. Dynamic characteristics *...continued*

GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit, see Figure 11

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_h	hold time	Dn to CP; see Figure 8								
		V_{CC} = 2.0 V	25	2	-	30	-	40	-	ns
		V_{CC} = 4.5 V	5	0	-	6	-	8	-	ns
		V_{CC} = 6.0 V	4	0	-	5	-	7	-	ns
f_{max}	maximum frequency	CP input; see Figure 8								
		V_{CC} = 2.0 V	6	25	-	4.8	-	4	-	MHz
		V_{CC} = 4.5 V	30	75	-	24	-	20	-	MHz
		V_{CC} = 5 V; C_L = 15 pF	-	83	-	-	-	-	-	MHz
		V_{CC} = 6.0 V	35	89	-	28	-	24	-	MHz
C_{PD}	power dissipation capacitance	per package; V_I = GND to V_{CC} [3]	-	32	-	-	-	-	-	pF
74HCT175										
t_{pd}	propagation delay	CP to Qn, $\overline{Q}$n; see Figure 8 [1]								
		V_{CC} = 4.5 V	-	19	33	-	41	-	50	ns
		V_{CC} = 5 V; C_L = 15 pF	-	16	-	-	-	-	-	ns
t_{PHL}	HIGH to LOW propagation delay	$\overline{MR}$ to Qn; see Figure 10								
		V_{CC} = 4.5 V	-	22	38	-	48	-	57	ns
		V_{CC} = 5 V; C_L = 15 pF	-	19	-	-	-	-	-	ns
		$\overline{MR}$ to $\overline{Q}$n; see Figure 10								
		V_{CC} = 4.5 V	-	19	35	-	44	-	53	ns
		V_{CC} = 5 V; C_L = 15 pF	-	16	-	-	-	-	-	ns
t_t	transition time	Qn output; see Figure 8 [2]								
		V_{CC} = 4.5 V	-	7	15	-	19	-	22	ns
t_W	pulse width	CP input; see Figure 8								
		V_{CC} = 4.5 V	20	12	-	25	-	30	-	ns
		$\overline{MR}$ input LOW; see Figure 10								
		V_{CC} = 4.5 V	20	11	-	25	-	30	-	ns
t_{rec}	recovery time	$\overline{MR}$ to CP; see Figure 10								
		V_{CC} = 4.5 V	5	–10	-	5	-	5	-	ns
t_{su}	set-up time	Dn to CP; see Figure 8								
		V_{CC} = 4.5 V	16	5	-	20	-	24	-	ns
t_h	hold time	Dn to CP; see Figure 8								
		V_{CC} = 4.5 V	5	0	-	5	-	5	-	ns

Table 7. Dynamic characteristics *...continued*

GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit, see Figure 11

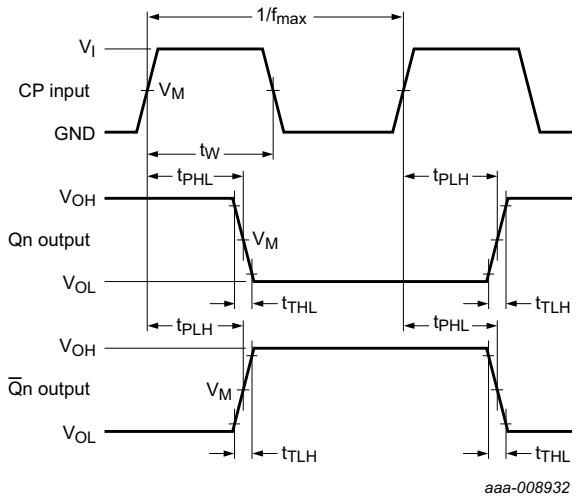
Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
f_{max}	maximum frequency	CP input; see Figure 8								
		V_{CC} = 4.5 V	25	49	-	20	-	17	-	MHz
		V_{CC} = 5 V; C_L = 15 pF	-	54	-	-	-	-	-	MHz
C_{PD}	power dissipation capacitance	per package; V_I = GND to V_{CC} − 1.5 V [3]	-	34	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PHL} and t_{PLH}.

[2] t_t is the same as t_{THL} and t_{TLH}.

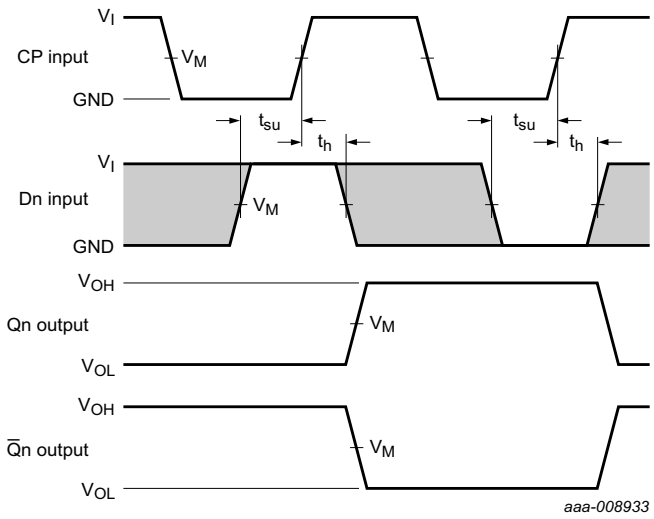
[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
$\Sigma (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V.

11. Waveforms



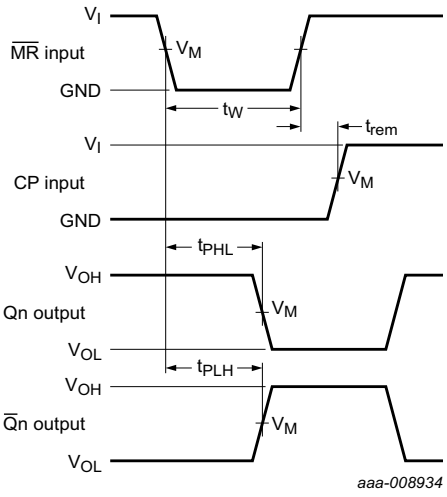
Measurement points are given in Table 8.

Fig 8. Input to output propagation delay, output transition time, clock input pulse width and maximum frequency



Measurement points are given in Table 8.

Fig 9. Data set-up and hold times for data input

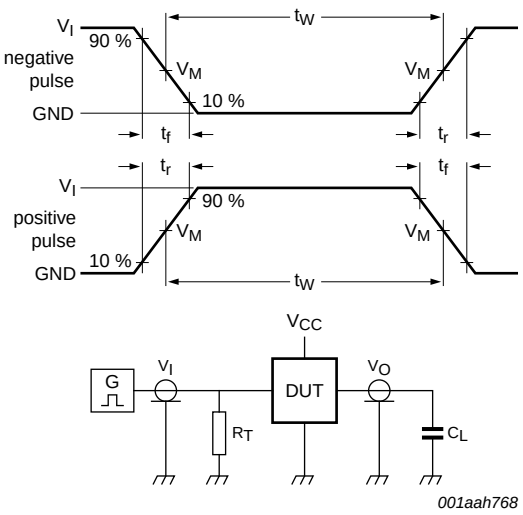


Measurement points are given in Table 8.

Fig 10. Master reset to output propagation delays, master reset pulse width and master reset to clock recovery time

Table 8. Measurement points

Type	Input		Output
	V_I	V_M	V_M
74HC175	V_{CC}	$0.5V_{CC}$	$0.5V_{CC}$
74HCT175	3 V	1.3 V	1.3 V



Test data is given in Table 9.

Definitions for test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

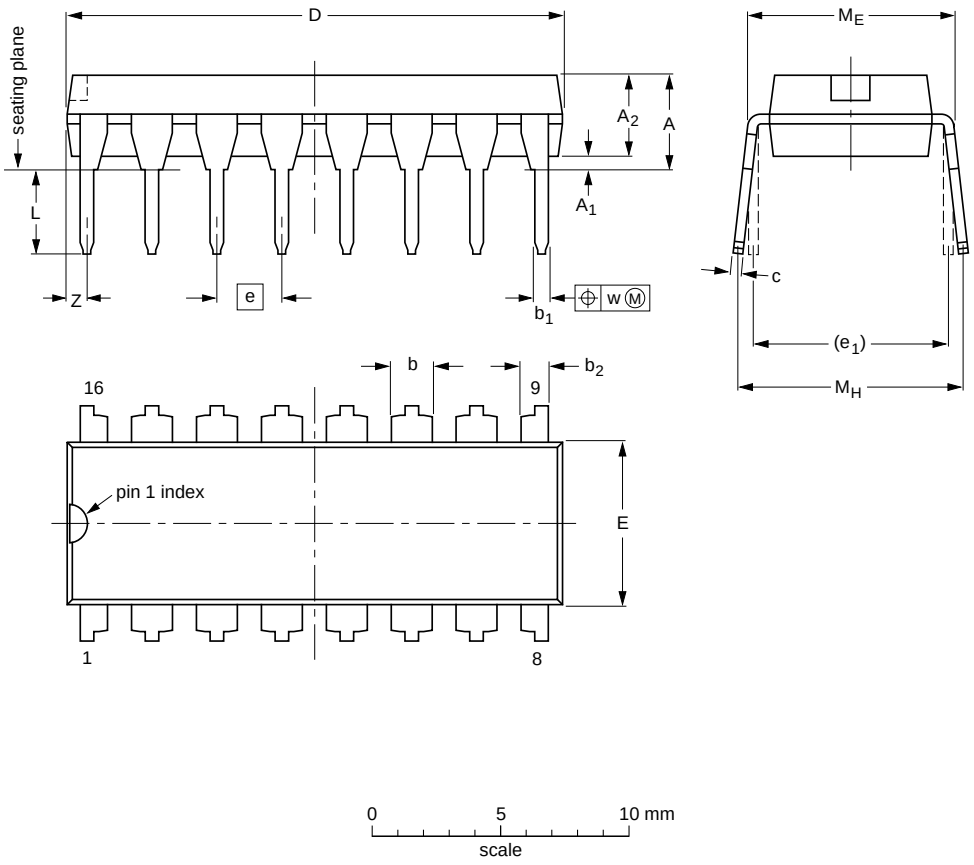
Fig 11. Test circuit for measuring switching times

Table 9. Test data

Type	Input		Load		Test
	V_I	t_r, t_f	C_L	R_L	
74HC175	V_{CC}	6 ns	15 pF, 50 pF	1 kΩ	t_{PLH}, t_{PHL}
74HCT175	3 V	6 ns	15 pF, 50 pF	1 kΩ	t_{PLH}, t_{PHL}

12. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil) **SOT38-4**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1 min.	A_2 max.	b	b_1	b_2	c	D (1)	E (1)	e	e_1	L	M_E	M_H	w	Z (1) max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.03

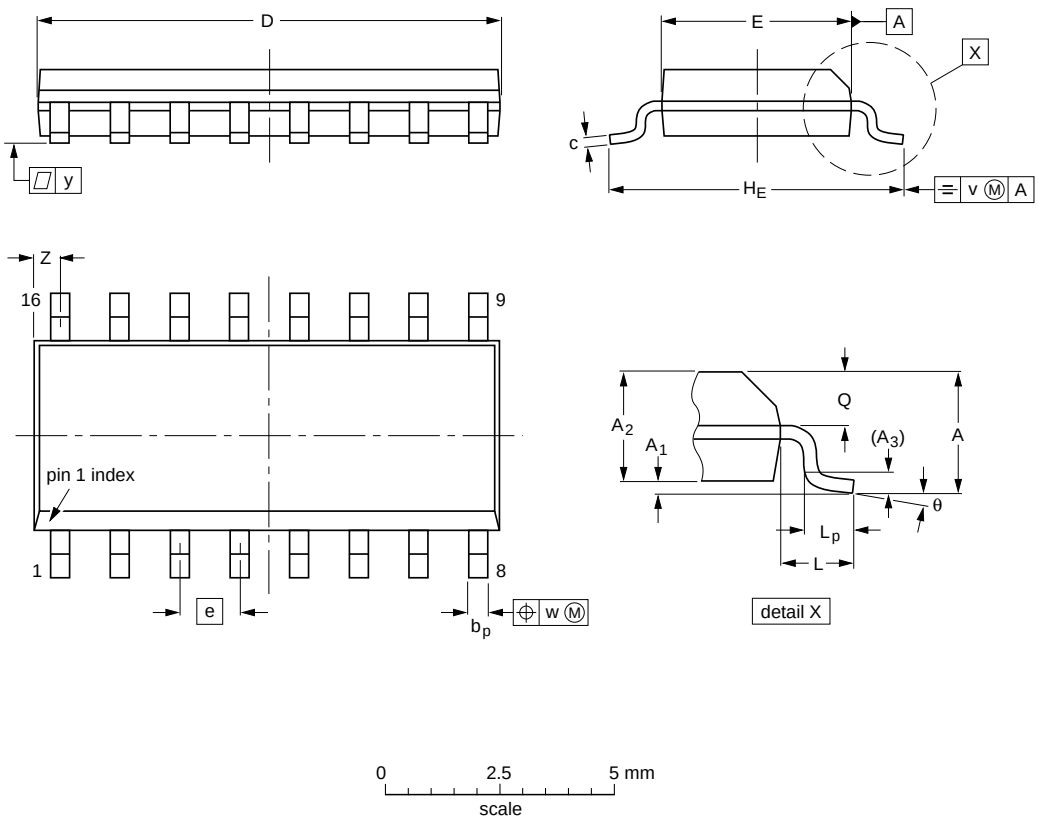
Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT38-4						~~95-01-14~~ 03-02-13

Fig 12. Package outline SOT38-4 (DIP16)

SO16: plastic small outline package; 16 leads; body width 3.9 mm **SOT109-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

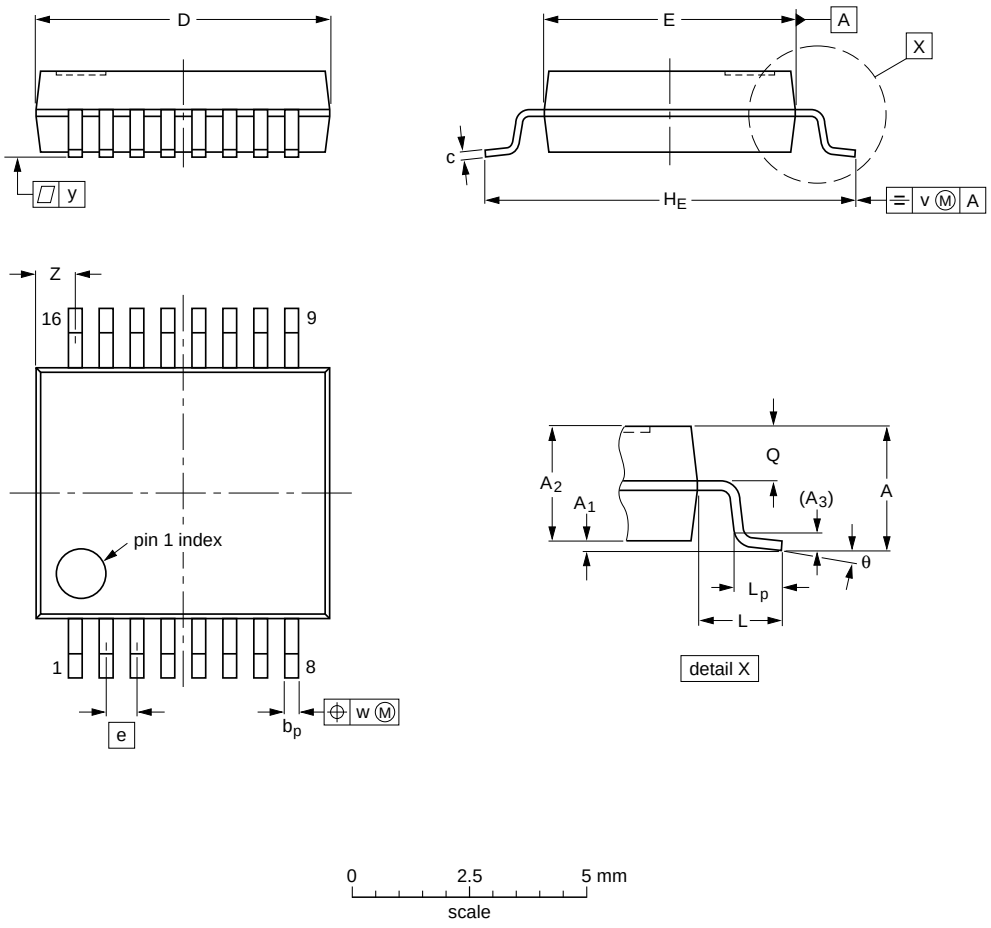
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				~~99-12-27~~ 03-02-19

Fig 13. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm **SOT338-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.00 0.55	8^o 0^o

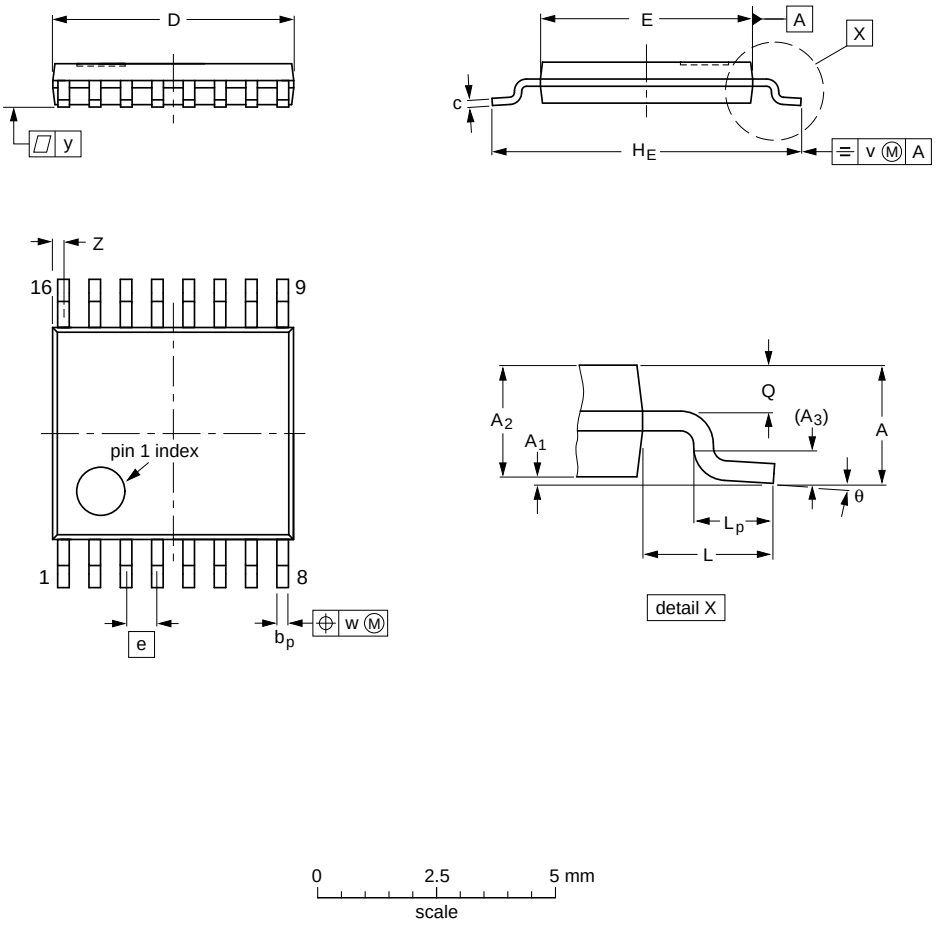
Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT338-1		MO-150				~~99-12-27~~ 03-02-19

Fig 14. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm **SOT403-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8^o 0^o

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				~~99-12-27~~ 03-02-18

Fig 15. Package outline SOT403-1 (TSSOP16)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT175 v.4	20140408	Product data sheet	-	74HC_HCT175 v.3
Modifications:	• General description corrected (errata).			
74HC_HCT175 v.3	20140331	Product data sheet	-	74HC_HCT175_CNV_2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate.			
74HC_HCT175_CNV_2	19980708	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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17. Contents

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